



DMNH6042SK3Q

#### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>C</sub> = +25°C
2014	50mΩ @ V <sub>GS</sub> = 10V	25A
60V	65mΩ @ V <sub>GS</sub> = 4.5V	22A

# **Description and Applications**

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported up by a PPAP and is ideal for use in:

- Driving Solenoids
- Driving Relays
- Power Management Functions

Top View

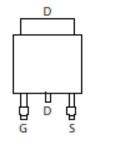


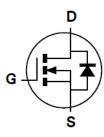
#### Features

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching Ensures More Reliable and Robust End Application
- Low On-Resistance
- Low Input Capacitance
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

## **Mechanical Data**

- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.315 grams (Approximate)





Equivalent Circuit

### Ordering Information (Note 5)

Part Number	Case	Packaging
DMNH6042SK3Q-13	TO252 (DPAK)	2,500/Tape & Reel

Pin Out Top View

Notes: 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.

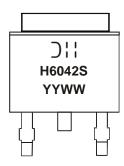
2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product\_compliance\_definitions.html.

5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## Marking Information



) : : = Manufacturer's Marking
H6042S = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 16 = 2016)
WW = Week Code (01 to 53)



# Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage	V <sub>DSS</sub>	60	V		
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 8) $V_{GS}$ = 10V	Steady State	$T_{C} = +25^{\circ}C$ $T_{C} = +70^{\circ}C$	ID	25 17	А
Pulsed Drain Current (10µs pulse, duty cycle = 1%)	I <sub>DM</sub>	40	А		
Maximum Continuous Body Diode Forward Current (Note 8)			Is	25	A
Avalanche Current (Note 9) L = 10mH			I <sub>AS</sub>	3.5	A
Avalanche Energy (Note 9) L = 10mH			E <sub>AS</sub>	65	mJ

### **Thermal Characteristics**

Characteristic	Symbol	Value	Units		
Total Power Dissipation (Note 6)		PD	2	W	
Thermal Desistance, Junction to Archient (Nate C)	Steady State	P	73	°C/W	
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	t<10s R <sub>0JA</sub>		°C/w	
Total Power Dissipation (Note 7)		PD	3.5	W	
Thermal Resistance, Junction to Ambient (Note 7)	Steady State	Devi	43	°C/W	
memai Resistance, sunction to Ambient (Note 7)	t<10s	R <sub>0JA</sub>	21		
Thermal Resistance, Junction to Case (Note 8)	R <sub>θJC</sub>	3.2			
Operating and Storage Temperature Range		TJ, TSTG	-55 to +175	°C	

# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 10)							
Drain-Source Breakdown Voltage	<b>BV</b> <sub>DSS</sub>	60	_	_	V	$V_{GS} = 0V, I_D = 250 \mu A$	
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	IDSS	_	—	1	μA	$V_{DS} = 60V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 10)						·	
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1.0	_	3.0	V	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$	
Static Drain-Source On-Resistance		_	30	50	mΩ	$V_{GS} = 10V, I_D = 6A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	45	65	11122	$V_{GS} = 4.5V, I_D = 6A$	
Diode Forward Voltage	V <sub>SD</sub>	_	0.8	1.2	V	$V_{GS} = 0V, I_{S} = 2.6A$	
DYNAMIC CHARACTERISTICS (Note 11)							
Input Capacitance	Ciss	_	584		pF		
Output Capacitance	Coss	_	83	—	pF	$V_{DS} = 25V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	Crss		24	_	pF		
Gate Resistance	Rg	—	3.8	—	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qg	_	4.2	—	nC		
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg	—	8.8	—	nC		
Gate-Source Charge	Q <sub>qs</sub>	_	1.8	—	nC	$V_{DS} = 44V, I_D = 5.2A$	
Gate-Drain Charge	Q <sub>gd</sub>	—	1.8	—	nC		
Turn-On Delay Time	t <sub>D(ON)</sub>	_	3.4		ns		
Turn-On Rise Time	t <sub>R</sub>	_	1.9	_	ns	$V_{GS} = 10V, V_{DS} = 30V,$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	10.1		ns	$R_G = 6\Omega, I_D = 1A$	
Turn-Off Fall Time	t <sub>F</sub>		4.5	_	ns	7	
Body Diode Reverse Recovery Time	t <sub>RR</sub>		12.9	_	ns		
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	_	5.4	_	nC	– I <sub>F</sub> = 2.6A, di/dt = 100A/μs	

Notes:

6. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.7. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

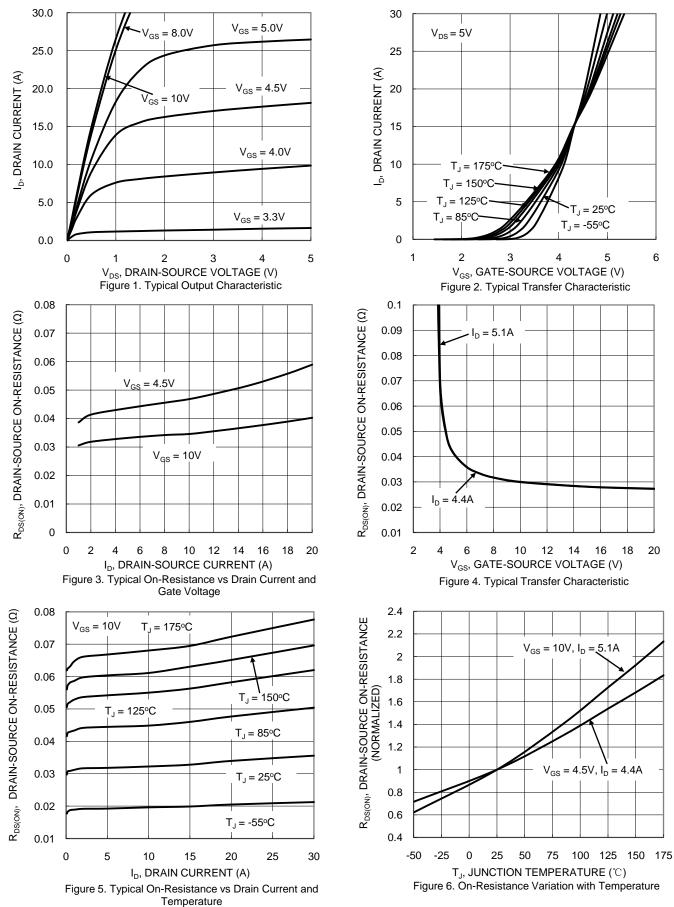
8. Thermal resistance from junction to soldering point (on the exposed drain pad).

9.  $I_{AS}$  and  $E_{AS}$  rating are based on low frequency and duty cycles to keep  $T_J = +25^{\circ}C$ .

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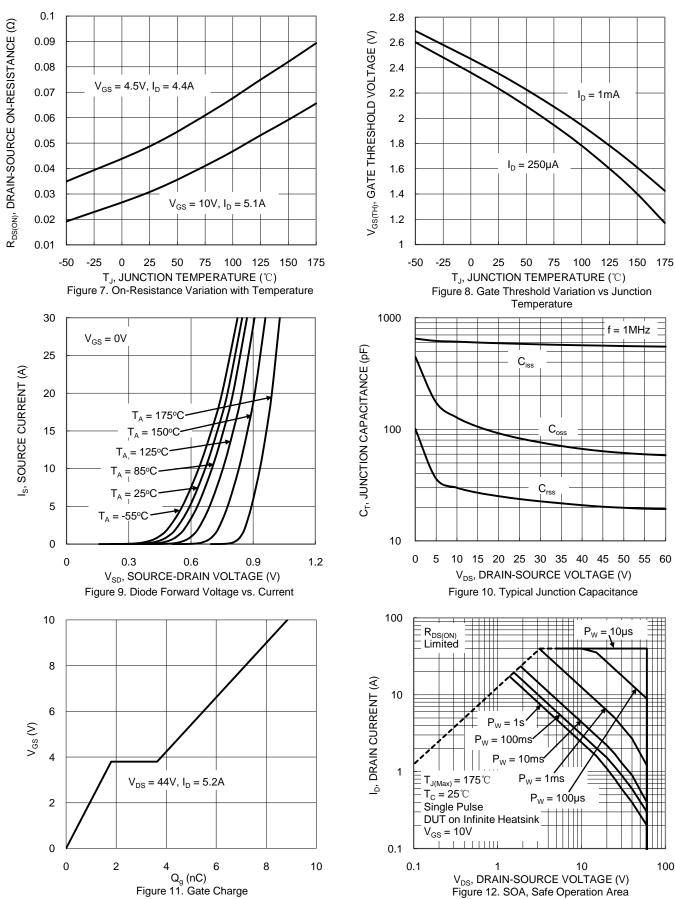
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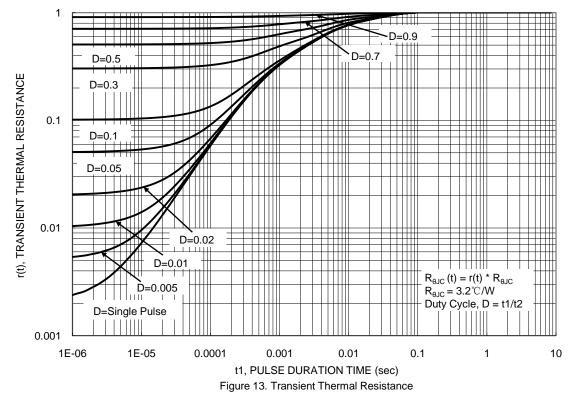
DMNH6042SK3Q Document number: DS38902 Rev. 2 - 2



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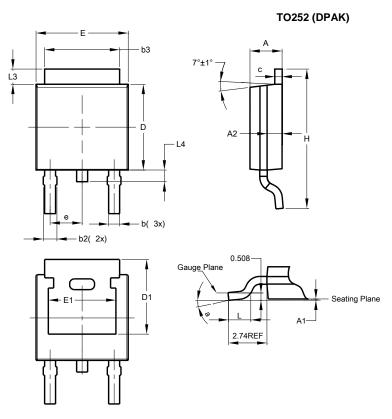






# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

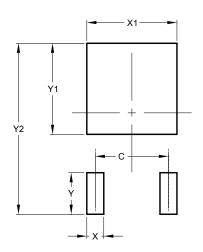


TO252 (DPAK)						
Dim	Min	Max	Тур			
Α	2.19	2.39	2.29			
A1	0.00	0.13	0.08			
A2	0.97	1.17	1.07			
b	0.64	0.88	0.783			
b2	0.76	1.14	0.95			
b3	5.21	5.46	5.33			
С	0.45	0.58	0.531			
D	6.00	6.20	6.10			
D1	5.21	-	-			
е	-	-	2.286			
Ε	6.45	6.70	6.58			
E1	4.32	-	-			
Н	9.40	10.41	9.91			
L	1.40	1.78	1.59			
L3	0.88	1.27	1.08			
L4	0.64	1.02	0.83			
а	0°	10°	-			
All	All Dimensions in mm					

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)



Dimensions	Value (in mm)
С	4.572
Х	1.060
X1	5.632
Y	2.600
Y1	5.700
Y2	10.700



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